

Please replace the Abstract of the Disclosure with the following replacement Abstract of the Disclosure:

A<sup>6</sup>  
--A solid-state imaging device having a gate structure including an oxide film and a nitride film includes upper layer films (for example, a planarization film, an insulating film, and a protective film) allowing ultraviolet rays having a wavelength of 400 nm or less to pass therethrough; and a metal made shield film or an organic film capable of absorbing the ultraviolet rays formed in such a manner as to cover a region of the gate structure (for example, an output gate and a reset gate), excluding a light receiving portion and a transfer portion, of the solid-state imaging device. With this configuration, it is possible to prevent the shift of a threshold voltage  $V_{th}$ , and hence to enhance the reliability of the transfer or reset of electric charges.--

IN THE CLAIMS

Please amend claims 1 and 3 as follows:

Sub B17  
A7  
1. (Amended) A solid-state imaging device having an output portion connected to an output end of a horizontal transfer register, the output portion having a gate structure including an oxide film and a nitride film, the solid-state imaging device comprising:

upper layer films allowing ultraviolet rays having a wavelength of 400 nm or less to pass therethrough; and

a metal made shield film formed in such a manner as to cover a region of said gate structure including an oxide film and a nitride film, excluding a light receiving portion and a transfer portion, of said solid-state imaging device.

Sub B37  
A8  
3. (Amended) A solid-state imaging device having an output portion connected to an output end of a horizontal transfer register, the output portion having a gate structure including an oxide film and a nitride film, the solid-state imaging device comprising:

upper layer films allowing ultraviolet rays having a wavelength of 400 nm or less to pass therethrough; and

an organic film capable of absorbing said ultraviolet rays, said organic film being formed in such a manner as to cover a region of said gate structure including an oxide film and a nitride film, excluding a light receiving portion and a transfer portion, of said solid-state imaging device.